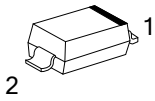
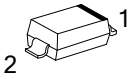
SILICON EPITAXIAL PLANAR DIODE



SOD-123



SOD-323

■ DESCRIPTION

The UTC **BAV20W** is a silicon epitaxial planar diode. The UTC **BAV20W** is suitable for general purpose application.

■ FEATURES

* Planar diode
* For general purpose application
* Low leakage current

■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment		Packing
		1	2	
BAV20WG-CA2-R	SOD-123	K	A	Tape Reel
BAV20WG-CB2-R	SOD-323	K	A	Tape Reel

Note: Pin Assignment: A: Anode K: Cathode

BAV20WG-CA2-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) CA2: SOD-123, CB2: SOD-323
(3)Green Package	(3) G: Halogen Free and Lead Free

■ MARKING

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Continuous Reverse Voltage	V_R	150	V
Forward DC Current at T_A=25°C (Note 2)	I_F	250	mA
Rectified Current (Average) Half Wave Rectification with Resist. Load at T_A=25°C (Note 2)	I_O	200	mA
Repetitive Peak Forward Current at f>50Hz, T_A=25°C (Note 2)	I_{FRM}	625	mA
Surge Forward Current at t<1s, T_J=25°C	I_{FSM}	1.0	A
Power Dissipation at T_A=25°C (Note 2)	P_D	410	mW
Junction Temperature	T_J	-55~+150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Valid provided that leads are kept at ambient temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	200	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V_F	I_F=100mA			1.00	V
		I_F=200mA			1.25	V
Leakage Current	I_R	V_R=150V			100	nA
		V_R=150V, T_J=100°C			15	μA
Dynamic Forward Resistance	R_F	I_F=10mA		5.0		Ω
Reverse Recovery Time	t_{rr}	I_F=30mA, I_R=30mA, Irr=3.0mA, R_L=100Ω			50	ns
Capacitance Between Terminals	C_T	V_R=0 , f=1.0MHz		1.5		pF